

GPP30A - GPP30M

AXIAL LEADED SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V CURRENT: 3.0 A

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

Case: DO-201AD, Molded Plastic

Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208

Polarity: Cathode Band

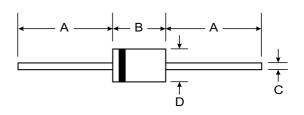
Weight: 1.2 grams (approx.)

Mounting Position: Any

Marking: Type Number







DO-201AD							
Dim	Min	Max					
Α	25.40						
В	7.20	9.50					
С	1.20	1.30					
D	4.80	5.30					
All Dimensions in mm							

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

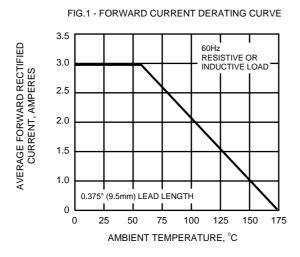
Characteristic	Symbol	GPP30A	GPP30B	GPP30D	GPP30G	GPP30J	GPP30K	GPP30M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1)	lo	3.0						Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	125.0						Α	
Forward Voltage @I _F = 3.0A	VFM	1.1						V	
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A$	İRM	5.0 100						μΑ	
Typical Junction Capacitance (Note 2)	Cj	40.0						pF	
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{ heta}JA$	20						K/W	
Operating Temperature Range	Tj	-65 to +125					°C		
Storage Temperature Range	Tstg	-65 to +150					°C		

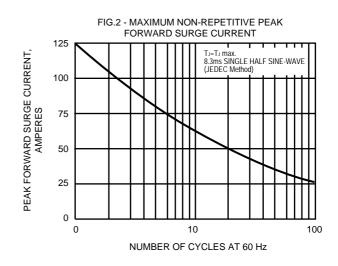
Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

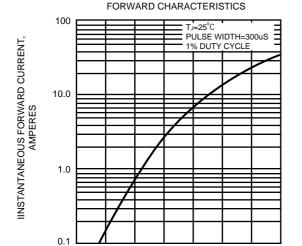
2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.



RATINGS AND CHARACTERISTIC CURVES GPP30A THRU GPP30M







1.0

INSTANTANEOUS FORWARD VOLTAGE,

0.6 0.7

FIG.3 - TYPICAL INSTANTANEOUS

